TOSHIBA Photocoupler GaAlAs Ired & Photo IC

6N135, 6N136

Digital Logic Isolation.

Line Receiver.

Power Supply Control

Switching Power Supply

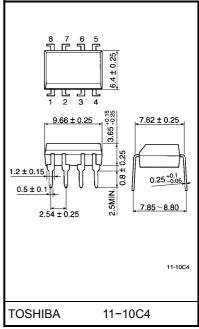
Transistor Inverter

The TOSHIBA 6N135 and 6N136 consists of a high emitting diode and a one chip photo diode—transistor.

Each unit is 8-lead DIP package.

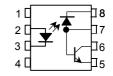
- Isolation voltage: 2500V_{rms} (min.)
- High speed: t_{pHL} , $t_{pLH} = 0.5\mu s$ (typ.) (RL = 1.9k Ω)
- TTL compatible
- If base pin is open, output signal will be noisy by environmental condition. For this base, TLP550 is suitable
- UL recognized: UL1577, file no. E67349

Unit in mm

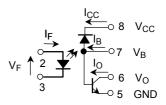


Weight: 0.54g

Pin Configurations



- 1 : N.C.
- 2 : ANODE
- 3 : CATHODE
- 4 : N.C.
- 5 : EMITTER
- 6: COLLECTOR
- 7: BASE, ANODE
- 8 : CATHODE



Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit
LED	Forward current	(Note 1)	lF	25	mA
	Pulse forward current	(Note 2)	I _{FP}	50	mA
	Total pulse forward current	(Note 3)	I _{FPT}	1	Α
	Reverse voltage		V_{R}	5	V
	Diode power dissipation	(Note 4)	P_{D}	45	mW
	Output current		Io	8	mA
Detector	Peak output current		I _{OP}	16	mA
	Emitter-base reverse voltage (p	V _{EB}	5	V	
	Supply voltage		V _{CC}	-0.5~15	V
	Output voltage		Vo	-0.5~15	V
	Base current (pin 7)		ΙΒ	5	mA
	Output power dissipation	(Note 5)	Po	100	mW
Opera	Operating temperature range		T _{opr}	-55~100	°C
Storag	Storage temperature range			-55~125	°C
Lead solder temperature (10s) (Note 6)			T _{sol}	260	°C
Isolation voltage (Note 7)		BVS	2500	V _{rms}	

- (Note 1) Derate 0.8mA above 70°C.
- (Note 2) 50% duty cycle, 1ms pulse width. Derate 1.6mA / °C above 70°C.
- (Note 3) Pulse width 1µs, 300pps.
- (Note 4) Derate 0.9mW / °C above 70°C.
- (Note 5) Derate 2mW / °C above 70°C.
- (Note 6) Soldering portion of lead: Up to 2mm from the body of the device.
- (Note 7) R.H. ≤ 60%, AC / 1min.

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Electrical Characteristics Over Recommended Temperature ($Ta = 0^{\circ}C \sim 70^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Test Condition	Min.	(**)Typ.	Max.	Unit
	6N135	CTR	I _F = 16mA, V _O = 0.4V	7	18	_	%
Current transfer	6N136	CIK	$V_{CC} = 4.5V$, Ta = 25°C (Note 8)	19	24	_	%
ratio	6N135	CTR	I _F = 16mA, V _O = 0.5V	5	13	_	%
	6N136	CIK	$V_{CC} = 4.5V$ (Note 1)	15	21	_	%
Logic low output	6N135	V _{OL}	I _F = 16mA, I _O = 1.1mA V _{CC} = 4.5V	ı	0.1	0.4	V
voltage	6N136	VOL	I _F = 16mA, I _O = 2.4mA V _{CC} = 4.5V	_	0.1	0.4	V
Logic high output current		lou	I _F = 0mA, V _O = V _{CC} = 5.5V Ta = 25°C	_	3	500	nA
		Іон	I _F = 0mA, V _O = V _{CC} = 15V Ta = 25°C	_	0.1	1	μА
		Іон	I _F = 0 mA, V _O = V _{CC} = 15V	_	_	50	μА
Logic low supply current		I _{CCL}	I _F = 16mA, V _O = open V _{CC} = 15V	1	40	1	μА
Logic high supply current		Icch	I _F = 0mA, V _O = open V _{CC} = 15V, Ta = 25°C	_	0.01	1	μА
		Icch	I_F = 0mA, V_O = open V_{CC} = 15V	_	_	2	μА
Input forward voltage		V _F	I _F = 16mA, Ta = 25°C		1.65	1.7	٧
Temperature coefficient of forward voltage		ΔV _F / ΔTa	I _F = 16mA	_	-1.9	_	mV / °C
Input reverse breakdown voltage		BV _R	I _R = 10μA, Ta = 25°C	5	_	_	V
Input capacitance		C _{IN}	f = 1MHz, V _F = 0		60	_	pF
Resistance (input-output)		R_{I-O}	V _{I-O} = 500V (Note 9) R.H. ≤ 60%	_	10 ¹²	_	Ω
Capacitance (input-output)		C_{I-O}	f = 1MHz (Note 9)	-	0.6	-	pF
Transistor DC current gain		h _{FE}	V _O = 5V, I _O = 3mA	_	80	_	_

^(**) All typicals at Ta = 25°C

Switching Specifications (unless otherwise specified. Ta = 25°C, V_{CC} = 5V, I_F = 16mA)

Characteristic		Symbol	Test Circuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay	6N135	t _{pHL}	1	$R_L = 4.1k\Omega$	_	0.2	1.5	μs
time to logic low at output	6N136			$R_L = 1.9k\Omega$	_	0.2	0.8	μs
Propagation delay	6N135	t _{pLH}	1	$R_L = 4.1k\Omega$	_	1.0	1.5	μs
time to logic high at output	6N136			$R_L = 1.9k\Omega$	_	0.5	0.8	μs
Common mode transient immunity	6N135	CM _H	2	$I_F = 0mA$ $V_{CM} = 10V_{p-p}$ $R_L = 4.1k\Omega$	_	1000	_	V / µs
at logic high level output (Note 10)	6N136			$I_F = 0mA$ $V_{CM} = 10V_{p-p}$ $R_L = 1.9k\Omega$	_	1000	_	V / µs
Common mode transient immunity	6N135	CML	2	$V_{CM} = 10V_{p-p}$ $R_L = 4.1k\Omega$ $I_F = 16mA$	_	-1000	_	V / µs
at logic low level output (Note 10)	6N136			$V_{CM} = 10V_{p-p}$ $R_L = 1.9k\Omega$ $I_F = 16mA$	_	-1000	_	V / µs
Bandwidth (Note 11)		BW	_	R _L = 100Ω	_	2	_	MHz

- (Note 8) DC current transfer ratio is defined as the ratio of output collector current, I_O , to the forward LED input current, I_F , times 100%.
- (Note 9) Device considered a two–terminal device: Pins 1, 2, 3, and 4 shorted together and pins 5, 6, 7 and 8 shorted together.
- (Note 10) Common mode transient immunity in logic high level is the maximum tolerable (positive) dv_{CM} / dt on the leading edge of the common mode pulse, V_{CM} , to assure that the output will remain in a logic high state (i.e., $V_O > 2.0V$).

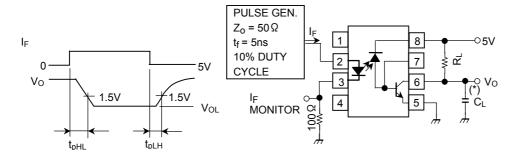
 Common mode transient immunity in logic low level is the maximum tolerable (negative) dv_{CM} / dt on

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the trailing edge of the common mode pulse signal, V_{CM} , to assure that the output will remain in a logic low state (i.e., $V_O < 0.8V$).

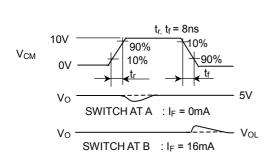
(Note 11) The frequency at which the AC output voltage is 3dB below the low frequency asymptote.

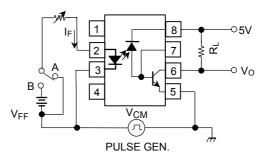
Test Circuit 1.

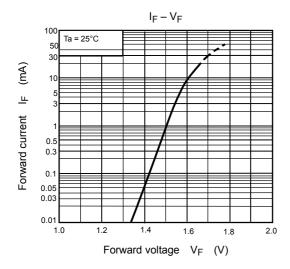


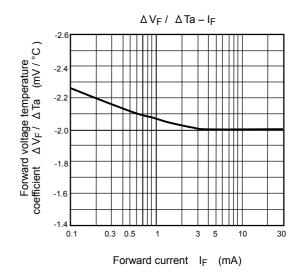
(*) C_L is approximately 15_PF which includes probe and stray wiring capacitance.

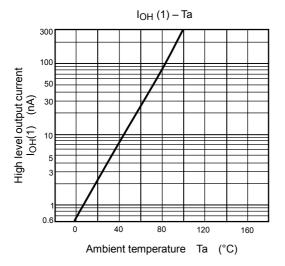
Test Circuit 2.

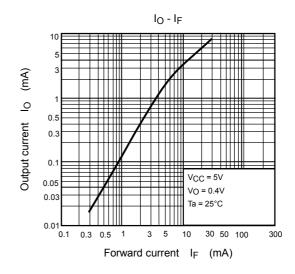


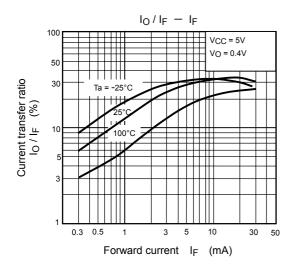


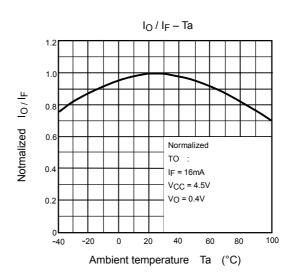


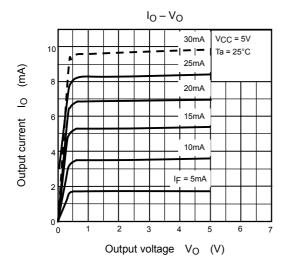


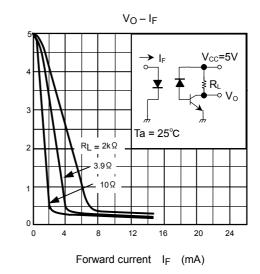






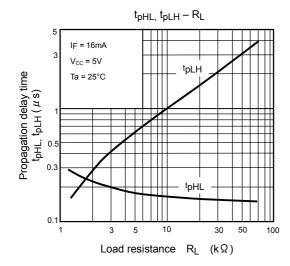






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Output voltage Vo



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